# 60V 17A N-Channel Enhancement Mode Power MOSFET

### **FEATURES**

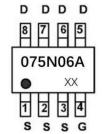
- RDSON $\leq$ 9m $\Omega$  @Vgs=10V, Id=15A
- Excellent RDS(ON) and Low Gate Charge
- · Lead free product is acquired

### **APPLICATION**

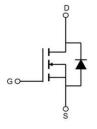
- Load Switch
- PWM Application
- · Power management



SOP-8 top view



**Marking and pin Assignment** 



**Schematic Diagram** 

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### **ASSEMBLY MESSAGE**

| Product Name | Marking       | Package | Packaging |
|--------------|---------------|---------|-----------|
| BXT090N06B   | 075N06A SOP-8 |         | Reel      |

### **ABSOLUTE MAXIMUM RATINGS** (Tc=25°C unless otherwise noted)

| Parameter                              |                | Symbol                            | Rating SOP-8    | Unit |    |
|--|----------------|-----------------------------------|-----------------|------|----|
| Drain-Source Voltage                   |                | V <sub>DSS</sub>                  | 60              | V    |    |
| Continuous (T <sub>C</sub> = 25°C)     |                | - 500                             | 17              | Α    |    |
| Drain Current                          | Cont           | inuous (T <sub>C</sub> = 100°C)   | l <sub>D</sub>  | 11   | Α  |
| Drain Current                          | Pulsed (Note1) |                                   | I <sub>DM</sub> | 68   | Α  |
| Gate-Source Voltage                    |                | √oltage                           |                 | ±20  | V  |
| Single Pulsed Avalanche Energy (note2) |                | e Pulsed Avalanche Energy (note2) |                 | 140  | mJ |
| Power Dissipation T <sub>C</sub> =25°C |                | T <sub>C</sub> =25°C              |                 | 4.8  | W  |
| Maximum Junction Temperature           |                | TJ                                | 150             | °C   |    |
| Storage Temperature Range              |                | T <sub>STG</sub>                  | -55 to 150      | °C   |    |

 $\begin{tabular}{ll} \textbf{Note:} & \textbf{1. Repetitive Rating: Pulse width limited by maximum junction temperature} \\ \end{tabular}$ 

2. EAS condition : TJ=25  $^{\circ}\text{C}$  ,VDD=30V,VG=10V,L=0.5mH,Rg=25 $\Omega$ ,IAS=23.7A

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## THERMAL CHARACTERISTICS

| Parameter                               | Symbol | Max.  | Unit  |  |
|---|--------|-------|-------|--|
| Farameter                               | Symbol | SOP-8 | Oiiit |  |
| Thermal Resistance, Junction to Ambient | Reja   | 26    | °C/W  |  |

## **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub>=25°C,unless otherwise Noted)

| Parameter                                       | Symbol              | Test Condition         | Min. | Тур. | Max. | Unit |
|---|---------------------|------------------------|------|------|------|------|
| OFF CHARACTERISTICS                             |                     |                        |      |      |      |      |
| Drain-Source Breakdown Voltage                  | BV <sub>DSS</sub>   | VGS=0V, ID=250µA       | 60   |      |      | V    |
| Zero Gate Voltage Drain Current                 | I <sub>DSS</sub>    | VDS=60V, VGS=0V        |      |      | 1    | uA   |
| Gate-Body Leakage Current, Forward              | I <sub>GSS</sub>    | VGS=20V                |      |      | 100  | nA   |
| Gate-Body Leakage Current, Reverse              |                     | VGS=-20V               |      |      | -100 | nA   |
| ON CHARACTERISTICS                              |                     | 1                      | •    | •    | •    |      |
| Gate Threshold Voltage                          | V <sub>GS(TH)</sub> | VDS=VGS, ID=250μA      | 1.0  | 1.7  | 2.5  | V    |
| Dunin Course On State Besistance                |                     | VGS=10V, ID=15A        |      | 6.7  | 9    | mΩ   |
| Drain-Source On-State Resistance                | R <sub>DS(ON)</sub> | VGS=4.5V, ID=10A       |      | 8.5  | 12   | mΩ   |
| DYNAMIC PARAMETERS                              |                     |                        |      |      |      |      |
| Input Capacitance                               | Ciss                | VDC-25V VCC-0V         |      | 1100 |      | pF   |
| Output Capacitance                              | Coss                | VDS=25V, VGS=0V,       |      | 302  |      | pF   |
| Reverse Transfer Capacitance                    | Crss                | f=1.0MHz               |      | 27   |      | pF   |
| SWITCHING PARAMETERS                            |                     |                        |      |      |      |      |
| Turn-ON Delay Time                              | $t_{D(ON)}$         |                        |      | 9.2  |      | ns   |
| Turn-ON Rise Time                               | t <sub>R</sub>      | VDD=30V, ID=15A, VGS = |      | 6.2  |      | ns   |
| Turn-OFF Delay Time                             | t <sub>D(OFF)</sub> | 10V, RG=1.8Ω           |      | 33.1 |      | ns   |
| Turn-OFF Fall-Time                              | t <sub>F</sub>      |                        |      | 7.6  |      | ns   |
| Total Gate Charge(Note3)                        | Q <sub>G</sub>      | VDS =30V, VGS =10V, ID |      | 99   |      | nC   |
| Gate Source Charge                              | Q <sub>G</sub> s    |                        |      | 12.6 |      | nC   |
| Gate Drain Charge                               | $Q_GD$              | =10A                   |      | 32.1 |      | nC   |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS |                     |                        |      |      |      |      |
| Drain-Source Diode Forward Voltage              | V <sub>SD</sub>     | IS=15A, VGS=0V         |      |      | 1.2  | V    |
| Diode Continuous Forward Current                | Is                  |                        |      |      | 17   | Α    |
| Maximum Pulsed Drain to Source                  | lsм                 |                        |      |      | 68   | _    |
| Diode Forward Current                           |                     |                        |      |      | 00   | Α    |
| Body Diode Reverse Recovery Time                | trr                 | IF=15A,dI/dt=100A/μs   |      | 30   |      | ns   |
| Body Diode Reverse Recovery Charge              | Qrr                 | ir-13A,ui/αι=100A/μS   |      | 49   |      | nC   |

Note: 3. Essentially independent of operating temperature

4

V<sub>GS</sub>=4.5V ID=10A

125

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150

175

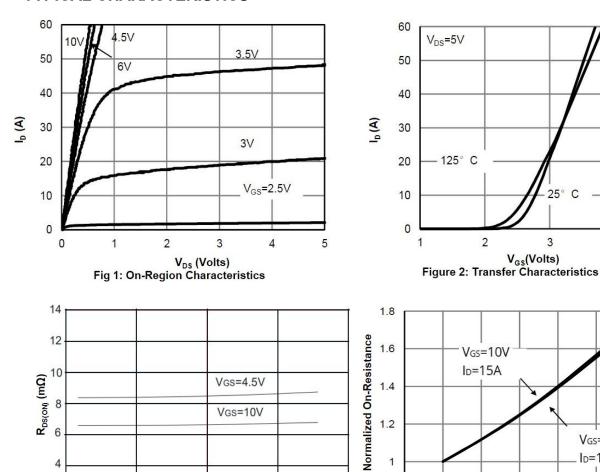
5



0

5

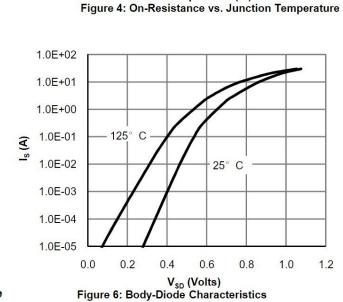
### **TYPICAL CHARACTERISTICS**



15

ID (A) Figure 3: On-Resistance vs. Drain Current and Gate Voltage

10



75

100

Temperature (℃)

3

1.2 BVDSS,(Normalized) Drain-to-Source Breakdown Voltage 1.15 1.1 1.05 1 0.95 0.9 0.85 -50 -25 0 25 50 75 100 125 150 TJ,Junction Temperature(°C)

Figure 5: Bvdss Variation with Temperature

0.8

0

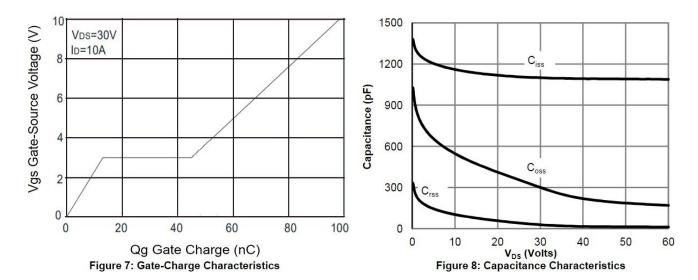
25

50

20



## **TYPICAL CHARACTERISTICS(Cont.)**



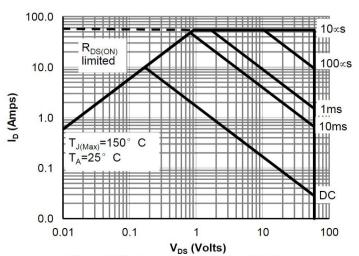
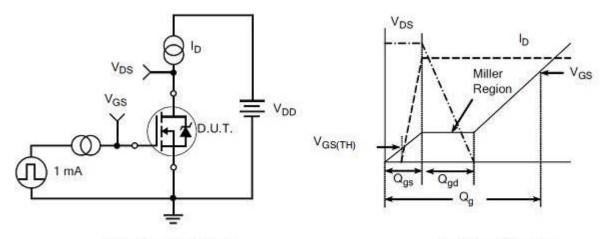


Figure 9: Maximum Forward Biased Safe Operating Area

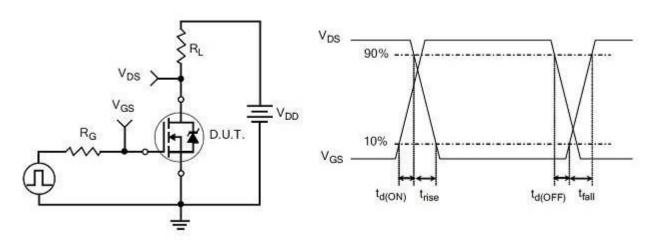


## **TEST CIRCUITS AND WAVEFORMS**



Gate Charge Test Circuit

Gate Charge Waveform



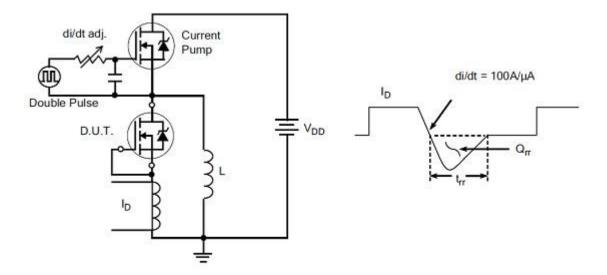
Resistive Switching Test Circuit

Resistive Switching Waveforms

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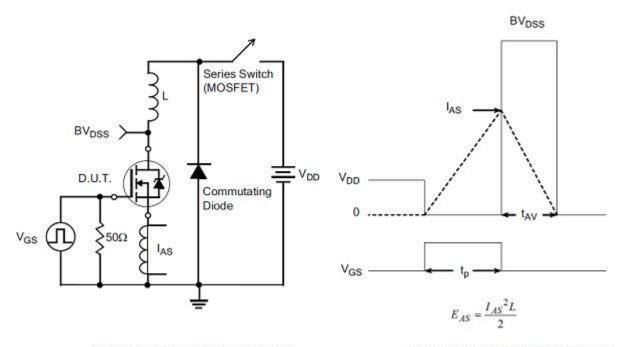


## TEST CIRCUITS AND WAVEFORMS(Cont.)



Diode Reverse Recovery Test Circuit

Diode Reverse Recovery Waveform



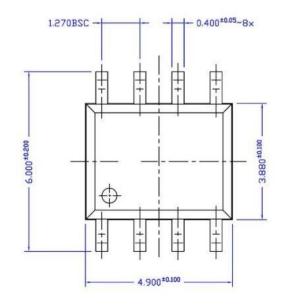
Unclamped Inductive Switching Test Circuit

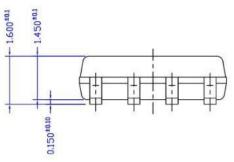
Unclamped Inductive Switching Waveforms

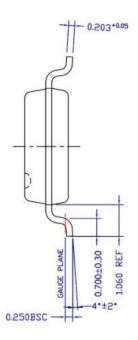
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# **SOP-8 Package**







Version: 1.0



## **Revision history**

## **Document revision history**

| Date        | Revision | Changes       |
|-------------|----------|---------------|
| 20-Mar-2021 | 1.0      | First release |
|             |          |               |
|             |          |               |
|             |          |               |

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